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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 4

## Complete if Known

Application Number	09/316,580
Filing Date	05/21/99
First Named Inventor	Jack H. Linn
Group Art Unit	2811
Examiner Name	Unknown
Attorney Docket Number	87552.99R134/SE-906D

## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
Loke	1	5,102,821		Moslehi	04/07/1992	
	2	4,980,306		Shimbo	12/25/1990	
	3	5,169,472		Goebel	12/08/1992	
	4	5,098,861		Blackstone	03/24/1992	
	5	5,387,555		Linn, et al.	02/1995	
	6	4,826,787		Muto, et al.	05/1989	
	7	2,974,075		Miller	03/1961	
	8	3,239,908		Nakamura	03/1966	
	9	3,689,357		Jordan	09/1972	
	10	4,638,552		Shimbo, et al.	01/1987	
	11	4,738,935		Shimbo, et al.	04/1988	
	12	4,854,986		Raby	08/1989	
	13	4,883,215		Geosele, et al.	11/1989	
	14	4,962,062		Uchiuyama, et al.	10/1990	
	15	5,131,968		Wells, et al.	07/1992	
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Loke	20	5,183,769		Rutter, et al.	02/1993	

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
Loke	21	JP	2-148821	JP		06/1990		
	22	JP	02-206118	JP	Hiroyuki Sugimoto	1990		
	23	JP	62-2122-148	JP		06/1987		
	24	EP	0 238 066	EP		09/1987		
	25	EP	0 256 397	EP		02/1998		
	26	EP	0 441 270 A3	EP		08/1991		
Loke	27	GB	2 242 313	GB		09/1991		

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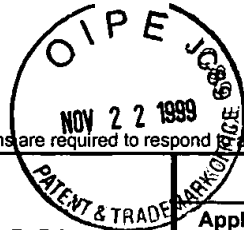
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First Named Inventor	Jack H. Linn
Group Art Unit	2811
Examiner Name	Unknown
Attorney Docket Number	87552.99R134/SE-906D

### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials <sup>2</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
Loke	28	M. Shimbo, et al., "Silicon-to-Silicon Direct Bonding Method", <u>Journal of Applied Physics</u> , Vol. 60(8), pp. 2987-2989, (October 1986).	
	29	Wolf, et al., "Silicon Processing for the VLSI Era", <u>Lattice Press</u> , Vol 1., pp. 390-391, 1986.	
	30	Sorab K. Ghandi, "Silicides", VLSI Fabrication Principles, <u>John Wiley &amp; Sons</u> , pp. 435-437, 1983.	
	31	S.P. Murarka, "Refractory Silicides For Integrated Circuits", <u>J. Vac. Science Technology</u> , Vol. 17(4), pp. 775-792, (July/August 1980).	
	32	Toshiba KK, "Bonding Method for Semiconductor Wafer", <u>Patent Abstracts</u> , Vol. 9, No. 227 E-355, A 60121715, June 11, 1985, Japan.	
	33	Fukuroda, et al., "Si Wafer Bonding with Ta Silicide Formation", <u>Japanese Journal of Applied Physics</u> , Vol. 30, No. 10A, pp. 1693-1695, (October 1, 1991), Tokyo, Japan.	
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	35	Astrova, et al., "The Nature of the P-Type Layer Formed In the Interface Region of Semiconducting Wafers During Solid-Phase Direct Bonding of Silicon", A.F. Ioffe Physicotechnical Institute, <u>Russian Academy of Sciences</u> , pp. 457-458, (July 18, 1992), New York.	
	36	Imthurn et al., "Bonded Silicon-On-Sapphire Wafers and Devices", <u>Journal of Applied Physics</u> , Vol. 72, No. 6, pp. 2526-2527, (September 15, 1992), New York.	
	37	Godbey, et al., "Fabrication of Bond and Etch-Back Silicon On Insulator Using Strained Si. sub 0.7 Ge, sub 0.3 Layer as An Eth Stop", <u>Journal of Electrochemical Society</u> , Vol. 137, No. 10. pp. 3219-3223, (October 1990), New Hampshire.	
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<b>Examiner Name</b>	Unknown
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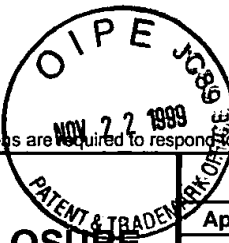
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Loke	42	Spierings and Haisma, "Diversity and Interfacial Phenomena in Direct Bonding", An Overview, Proceedings First International Symposium on Semiconductor Wafer Bonding, <u>Electrochemical Society Meeting</u> , pp. 18-32, (October 1991), Phoenix, Arizona.	
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↓	44	J. Haisma, et al. "Silicon On-Insulator Wafer Bonding Wafer Thinning Technological Evaluations", <u>Japanese Journal Appl. Phys.</u> , Vol. 28, No. 8, pp. 1426-1443, (1989).	
Loke		**The above cited references were included with prior filed IDS's for application numbers 08/915,841, 08/681,038, 08/351,933, 07/939,786, 07/834,439, 07/921,197, 08/430,312.	

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